SK Hynix announced the start of the supply of a new generation of DRAM mobile memory, designed to reduce overheating in smartphones. The manufacturer claims that the thermal conductivity of the chips is increased by 350%, which should solve the problem of drop in performance at high loads.

The novelty is based on a material called High-K Epoxy Molding Compound. Due to this change, thermal resistance in the vertical direction decreased by 47%. Such refinement is especially important for modern smartphones, where memory chips are often located on top of the processor. In intensive work, this design leads to heat accumulation and worsening the speed of the device.

The SK Hynix solution should affect not only smartphone stability, but also the duration of the battery. A more effective heat removal will reduce the risk of overheating and will allow devices to maintain the declared characteristics longer.

The company explained that it has achieved an improvement in thermal conductivity by adding aluminum oxide to silicon oxide used in the compound. This combination allows you to more effectively distribute heat inside the smartphone.